

This diagram shows a cross-sectional view of a semiconductor device. A central channel region is defined by a series of gates (34a, 35, 34b) and is doped with N^+ and N^- ions. The channel is flanked by N^+ and P^- regions. The device is mounted on a substrate (1) with a passivation layer (2). The gates are labeled 31, 32, 33, and 36. The channel is labeled 3. The substrate is labeled 1. The passivation layer is labeled 2. The gates are labeled 31, 32, 33, and 36. The channel is labeled 3. The substrate is labeled 1. The passivation layer is labeled 2.



FIG. 33

